

SGF23N60UFD

Ultra-Fast IGBT

General Description

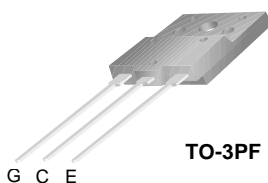
Fairchild's Insulated Gate Bipolar Transistor(IGBT) UFD series provides low conduction and switching losses. UFD series is designed for the applications such as motor control and general inverters where High Speed Switching is required.

Features

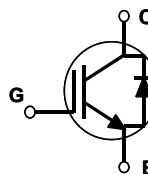
- High Speed Switching
- Low Saturation Voltage : $V_{CE(sat)} = 2.1\text{ V @ } I_C = 12\text{ A}$
- High Input Impedance
- CO-PAK, IGBT with FRD : $t_{rr} = 42\text{ ns (typ.)}$

Application

AC & DC Motor controls, General Purpose Inverters, Robotics, Servo Controls



TO-3PF



Absolute Maximum Ratings $T_C = 25^\circ\text{C}$ unless otherwise noted

Symbol	Description	SGF23N60UFD	Units
V_{CES}	Collector-Emitter Voltage	600	V
V_{GES}	Gate-Emitter Voltage	± 20	V
I_C	Collector Current @ $T_C = 25^\circ\text{C}$	23	A
	Collector Current @ $T_C = 100^\circ\text{C}$	12	A
$I_{CM(1)}$	Pulsed Collector Current	92	A
I_F	Diode Continuous Forward Current @ $T_C = 100^\circ\text{C}$	12	A
I_{FM}	Diode Maximum Forward Current	92	A
P_D	Maximum Power Dissipation @ $T_C = 25^\circ\text{C}$	75	W
	Maximum Power Dissipation @ $T_C = 100^\circ\text{C}$	30	W
T_J	Operating Junction Temperature	-55 to +150	$^\circ\text{C}$
T_{stg}	Storage Temperature Range	-55 to +150	$^\circ\text{C}$
T_L	Maximum Lead Temp. for Soldering Purposes, 1/8" from Case for 5 Seconds	300	$^\circ\text{C}$

Notes :

(1) Repetitive rating : Pulse width limited by max. junction temperature

Thermal Characteristics

Symbol	Parameter	Typ.	Max.	Units
$R_{\theta JC}$ (IGBT)	Thermal Resistance, Junction-to-Case	--	1.6	$^\circ\text{C/W}$
$R_{\theta JC}$ (DIODE)	Thermal Resistance, Junction-to-Case	--	3.0	$^\circ\text{C/W}$
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	--	40	$^\circ\text{C/W}$

Electrical Characteristics of IGBT $T_C = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
Off Characteristics						
BV_{CES}	Collector-Emitter Breakdown Voltage	$V_{GE} = 0V, I_C = 250\mu A$	600	--	--	V
$\Delta BV_{CES}/\Delta T_J$	Temperature Coeff. of Breakdown Voltage	$V_{GE} = 0V, I_C = 1mA$	--	0.6	--	$V/^\circ C$
I_{CES}	Collector Cut-Off Current	$V_{CE} = V_{CES}, V_{GE} = 0V$	--	--	250	μA
I_{GES}	G-E Leakage Current	$V_{GE} = V_{GES}, V_{CE} = 0V$	--	--	± 100	nA

On Characteristics

$V_{GE(th)}$	G-E Threshold Voltage	$I_C = 12mA, V_{CE} = V_{GE}$	3.5	4.5	6.5	V
$V_{CE(sat)}$	Collector to Emitter Saturation Voltage	$I_C = 12A, V_{GE} = 15V$	--	2.1	2.6	V
		$I_C = 23A, V_{GE} = 15V$	--	2.6	--	V

Dynamic Characteristics

C_{ies}	Input Capacitance	$V_{CE} = 30V, V_{GE} = 0V,$ $f = 1MHz$	--	720	--	pF
C_{oes}	Output Capacitance		--	100	--	pF
C_{res}	Reverse Transfer Capacitance		--	25	--	pF

Switching Characteristics

$t_{d(on)}$	Turn-On Delay Time	$V_{CC} = 300V, I_C = 12A,$ $R_G = 23\Omega, V_{GE} = 15V,$ Inductive Load, $T_C = 25^\circ C$	--	17	--	ns
t_r	Rise Time		--	27	--	ns
$t_{d(off)}$	Turn-Off Delay Time		--	60	130	ns
t_f	Fall Time		--	70	150	ns
E_{on}	Turn-On Switching Loss		--	115	--	μJ
E_{off}	Turn-Off Switching Loss		--	135	--	μJ
E_{ts}	Total Switching Loss	--	250	400	μJ	
$t_{d(on)}$	Turn-On Delay Time	$V_{CC} = 300V, I_C = 12A,$ $R_G = 23\Omega, V_{GE} = 15V,$ Inductive Load, $T_C = 125^\circ C$	--	23	--	ns
t_r	Rise Time		--	32	--	ns
$t_{d(off)}$	Turn-Off Delay Time		--	100	200	ns
t_f	Fall Time		--	220	250	ns
E_{on}	Turn- On Switching Loss		--	205	--	μJ
E_{off}	Turn- Off Switching Loss		--	320	--	μJ
E_{ts}	Total Switching Loss	--	525	800	μJ	
Q_g	Total Gate Charge	$V_{CE} = 300V, I_C = 12A,$ $V_{GE} = 15V$	--	49	80	nC
Q_{ge}	Gate-Emitter Charge		--	11	17	nC
Q_{gc}	Gate-Collector Charge		--	14	22	nC
L_e	Internal Emitter Inductance	Measured 5mm from PKG	--	14	--	nH

Electrical Characteristics of DIODE $T_C = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units	
V_{FM}	Diode Forward Voltage	$I_F = 12A$	$T_C = 25^\circ C$	--	1.4	1.7	V
			$T_C = 100^\circ C$	--	1.3	--	
t_{rr}	Diode Reverse Recovery Time	$I_F = 12A,$ $di/dt = 200A/\mu s$	$T_C = 25^\circ C$	--	42	60	ns
			$T_C = 100^\circ C$	--	80	--	
I_{rr}	Diode Peak Reverse Recovery Current	$I_F = 12A,$ $di/dt = 200A/\mu s$	$T_C = 25^\circ C$	--	3.5	6.0	A
			$T_C = 100^\circ C$	--	5.6	--	
Q_{rr}	Diode Reverse Recovery Charge	$I_F = 12A,$ $di/dt = 200A/\mu s$	$T_C = 25^\circ C$	--	80	180	nC
			$T_C = 100^\circ C$	--	220	--	

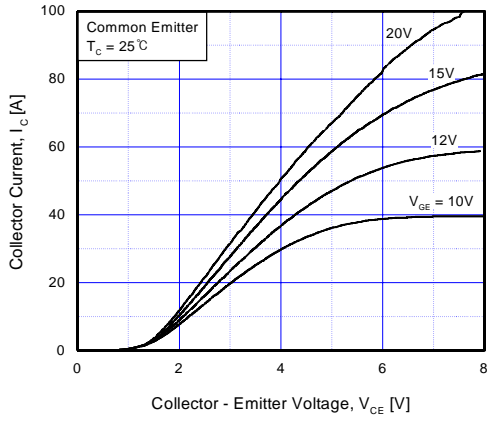


Fig 1. Typical Output Characteristics

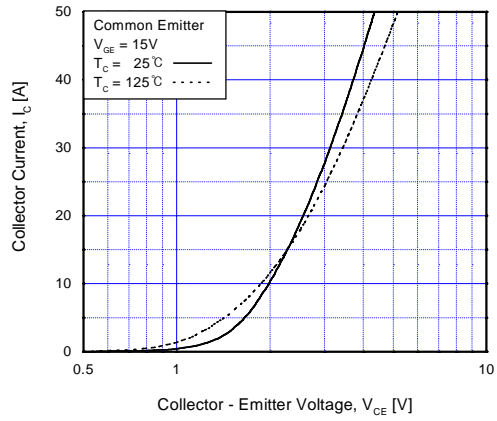


Fig 2. Typical Saturation Voltage Characteristics

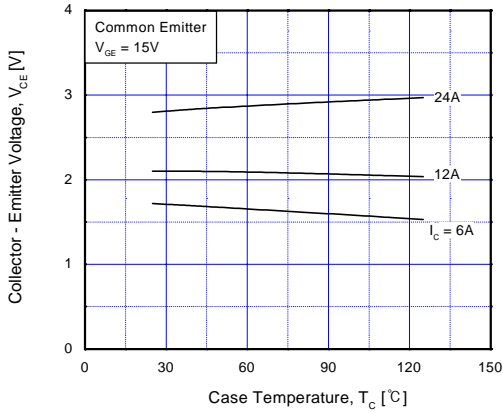


Fig 3. Saturation Voltage vs. Case Temperature at Variant Current Level

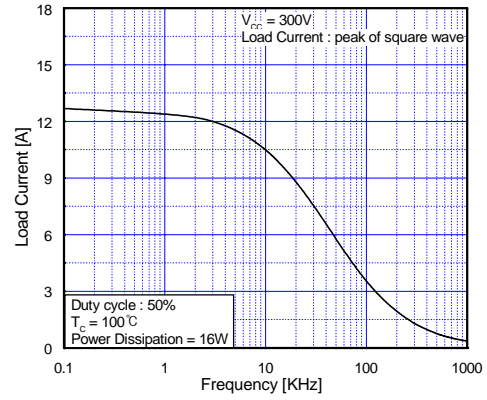


Fig 4. Load Current vs. Frequency

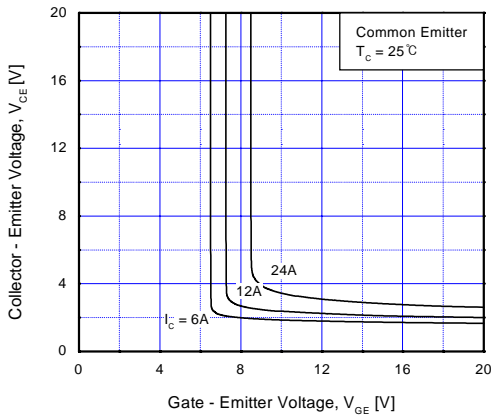


Fig 5. Saturation Voltage vs. V_{GE}

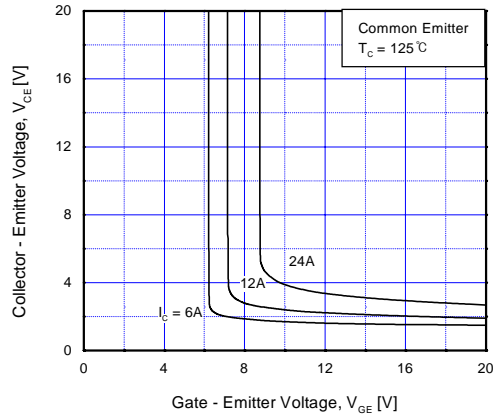


Fig 6. Saturation Voltage vs. V_{GE}

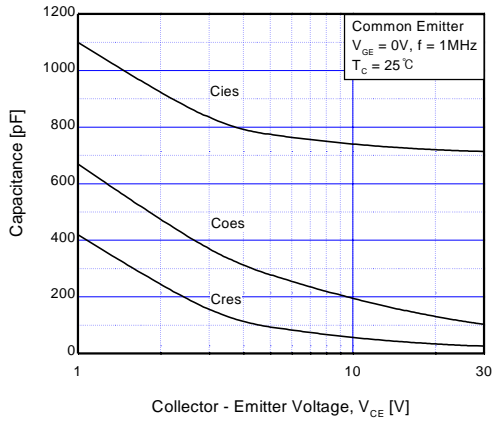


Fig 7. Capacitance Characteristics

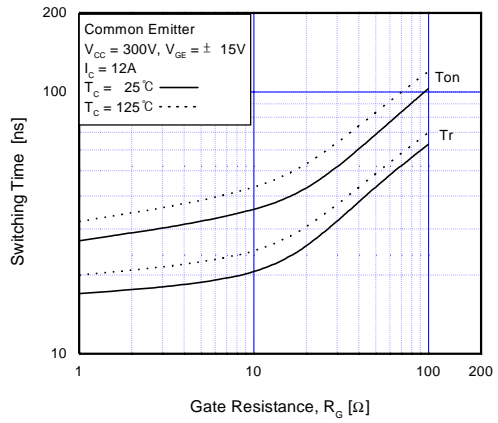


Fig 8. Turn-On Characteristics vs. Gate Resistance

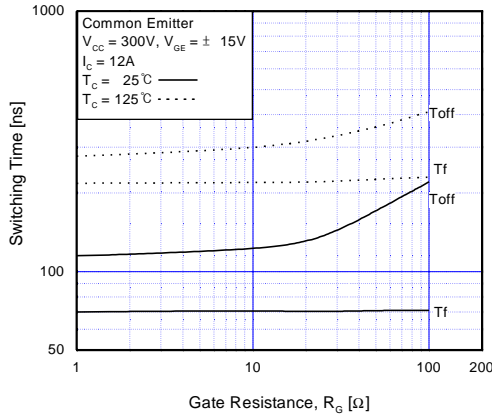


Fig 9. Turn-Off Characteristics vs. Gate Resistance

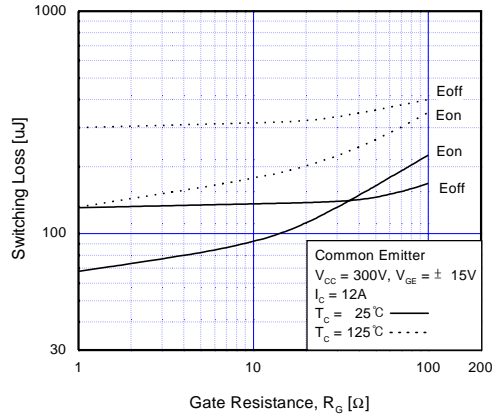


Fig 10. Switching Loss vs. Gate Resistance

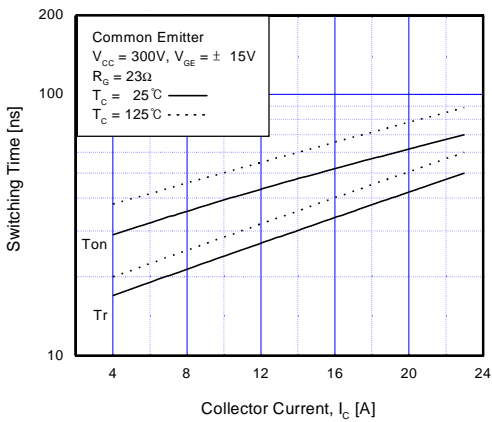


Fig 11. Turn-On Characteristics vs. Collector Current

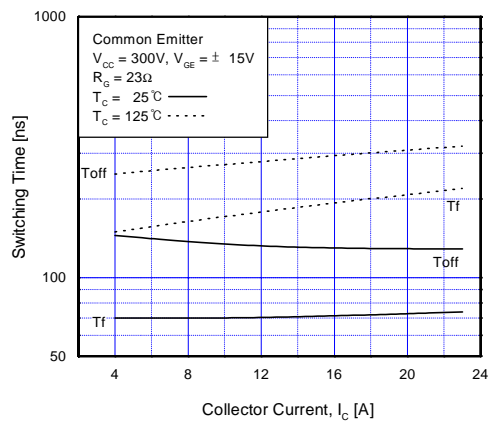


Fig 12. Turn-Off Characteristics vs. Collector Current

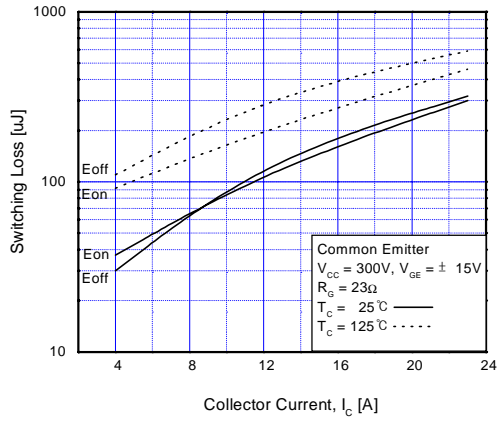


Fig 13. Switching Loss vs. Collector Current

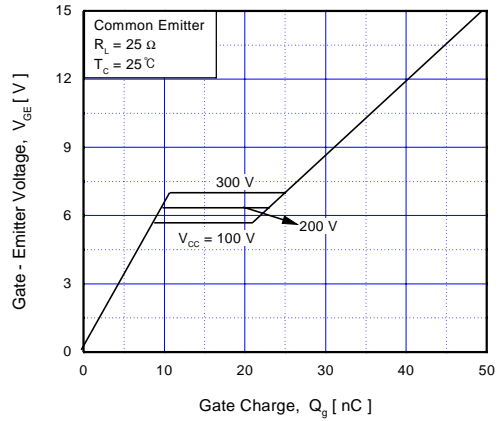


Fig 14. Gate Charge Characteristics

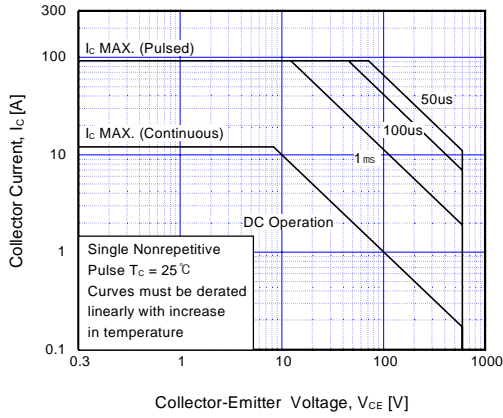


Fig 15. SOA Characteristics

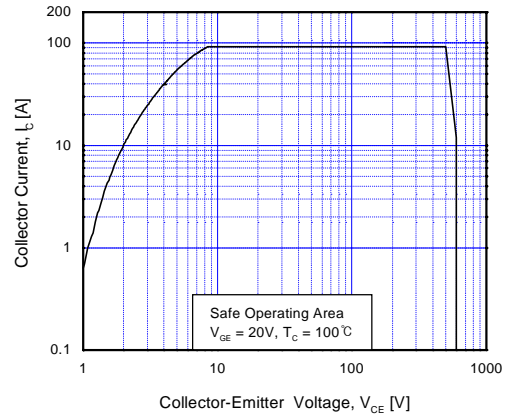


Fig 16. Turn-Off SOA Characteristics

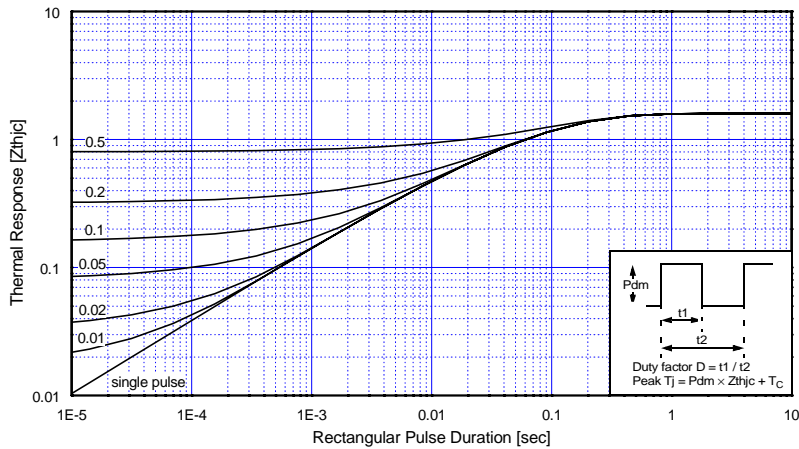


Fig 17. Transient Thermal Impedance of IGBT

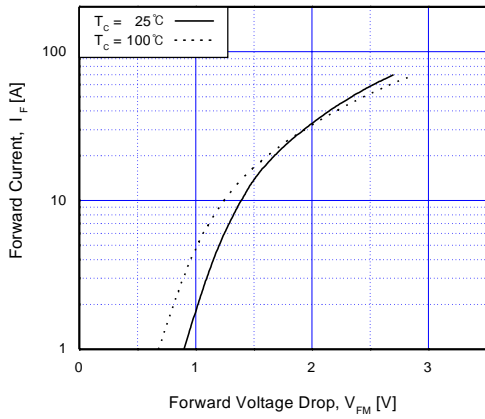


Fig 18. Forward Characteristics

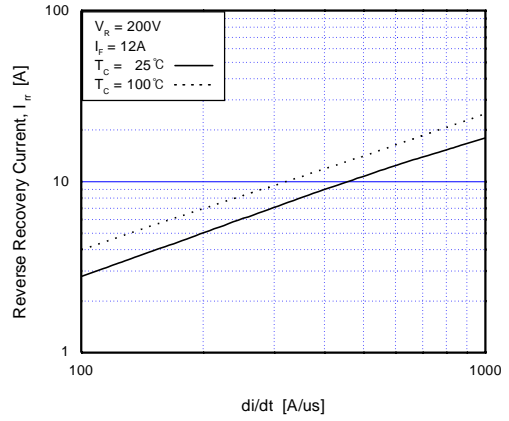


Fig 19. Reverse Recovery Current

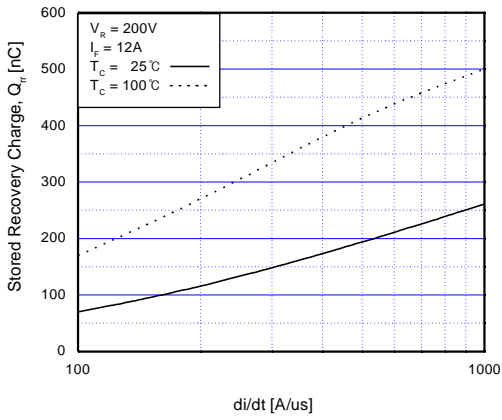


Fig 20. Stored Charge

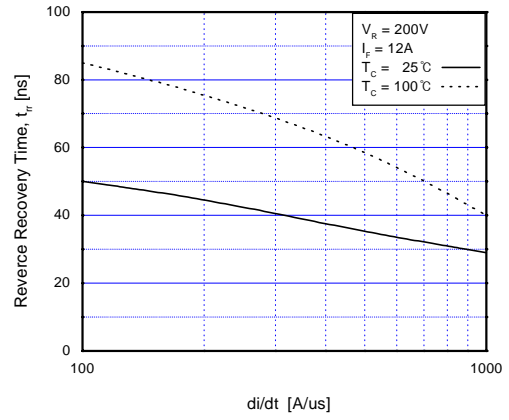
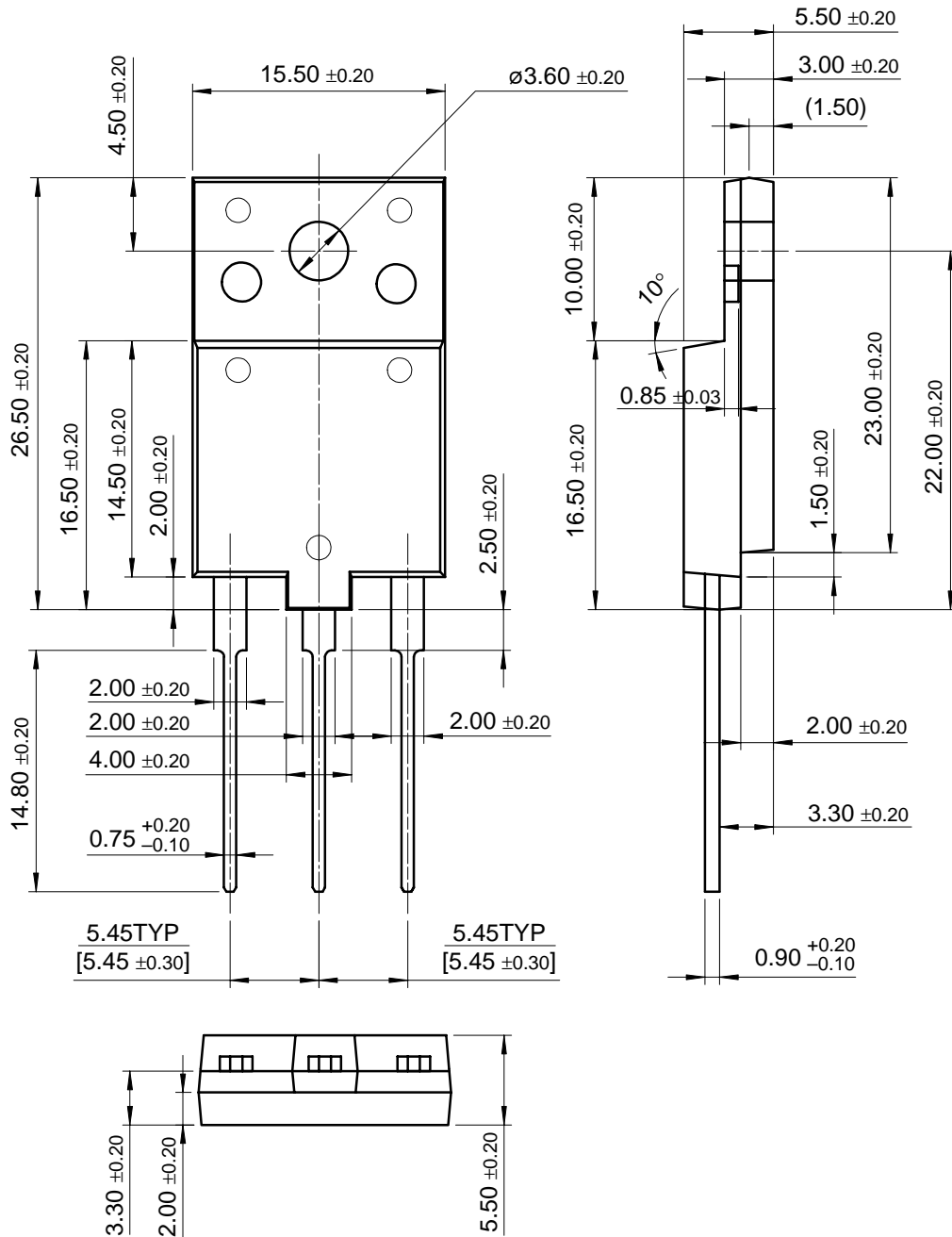


Fig 21. Reverse Recovery Time

Package Dimension

TO-3PF (FS PKG CODE AG)



Dimensions in Millimeters

TRADEMARKS

The following are registered and unregistered trademarks Fairchild Semiconductor owns or is authorized to use and is not intended to be an exhaustive list of all such trademarks.

ACE _x TM	FAST [®]	OPTOPLANAR TM	STAR*POWER TM
Bottomless TM	FAST _r TM	PACMAN TM	Stealth TM
CoolFET TM	FRFET TM	POP TM	SuperSOT TM -3
CROSSVOLT TM	GlobalOptoisolator TM	Power247 TM	SuperSOT TM -6
DenseTrench TM	GTO TM	PowerTrench [®]	SuperSOT TM -8
DOME TM	HiSeC TM	QFET TM	SyncFET TM
EcoSPARK TM	ISOPLANAR TM	QS TM	TruTranslation TM
E ² CMOS TM	LittleFET TM	QT Optoelectronics TM	TinyLogic TM
EnSigna TM	MicroFET TM	Quiet Series TM	UHC TM
FACT TM	MICROWIRE TM	SLIENT SWITCHER [®]	UltraFET [®]
FACT Quiet Series TM	OPTOLOGIC TM	SMART START TM	VCX TM

STAR*POWER is used under license

DISCLAIMER

FAIRCHILD SEMICONDUCTOR RESERVES THE RIGHT TO MAKE CHANGES WITHOUT FURTHER NOTICE TO ANY PRODUCTS HEREIN TO IMPROVE RELIABILITY, FUNCTION OR DESIGN. FAIRCHILD DOES NOT ASSUME ANY LIABILITY ARISING OUT OF THE APPLICATION OR USE OF ANY PRODUCT OR CIRCUIT DESCRIBED HEREIN; NEITHER DOES IT CONVEY ANY LICENSE UNDER ITS PATENT RIGHTS, NOR THE RIGHTS OF OTHERS.

LIFE SUPPORT POLICY

FAIRCHILD'S PRODUCTS ARE NOT AUTHORIZED FOR USE AS CRITICAL COMPONENTS IN LIFE SUPPORT DEVICES OR SYSTEMS WITHOUT THE EXPRESS WRITTEN APPROVAL OF FAIRCHILD SEMICONDUCTOR INTERNATIONAL.

As used herein:

1. Life support devices or systems are devices or systems which, (a) are intended for surgical implant into the body, or (b) support or sustain life, or (c) whose failure to perform when properly used in accordance with instructions for use provided in the labeling, can be reasonably expected to result in significant injury to the user.
2. A critical component is any component of a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.

PRODUCT STATUS DEFINITIONS

Definition of Terms

Datasheet Identification	Product Status	Definition
Advance Information	Formative or In Design	This datasheet contains the design specifications for product development. Specifications may change in any manner without notice.
Preliminary	First Production	This datasheet contains preliminary data, and supplementary data will be published at a later date. Fairchild Semiconductor reserves the right to make changes at any time without notice in order to improve design.
No Identification Needed	Full Production	This datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice in order to improve design.
Obsolete	Not In Production	This datasheet contains specifications on a product that has been discontinued by Fairchild semiconductor. The datasheet is printed for reference information only.